PTO/SB/084(10-01
Approved for use through 10/31/2002, OMS 651-0031
Patent & Trademark Office, U.S. GEPARTMENT OF CONNERCE

Substitute for form 1449APTO
INSORMATION DISCLOSURE
(Use as many sheets as note only)

ART DESCRIPTION OF THE PROPERTY OF THE

Complete if Known	
Application Number	09/944985
Filing Date	August 30, 2001
First Named Inventor	Bhattacharyya, Arup
Group Art Unit	2811
Examiner Name	Tran, Thien
· · · · · · · · · · · · · · · · · · ·	

Sheet 1 of 3

Attorney Docket No: 1303.023US1

1		USPA	ATENT DOCUMENT	S		
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
TŢ	US- 2001/0013621	08/01/2001	Kazuo, Nakazato	257	314	12/08/2000
TT	US- 2002/0106536	08/08/2002	Lee, Jongho, et al.	428	702	02/02/2001
Π	US- 2003/0042527	03/06/2003	Forbes, Leonard, et al.	257	315	08/30/2001
П	US- 2003/0042532	03/06/2003	Forbes, Leonard	257	316	08/30/2001
Tī	US- 2003/0043622	03/06/2003	Forbes, Leondard	365	185.05	08/30/2001
TT	US- 2003/0043630	03/06/2003	Forbes, Leonard, et al.	365	185.26	08/30/2001
т	US- 2003/0043632	03/06/2003	Forbes, Leonard	365	185.28	08/30/2001
TI	US- 2003/0043633	03/06/2003	Forbes, Leonard, et al.	365	185.28	12/20/2001
П	US- 2003/0043637	03/06/2003	Forbes, Leonard , et al.	365	185.33	08/30/2001
77	US- 2003/0045082	03/06/2003	Eldridge, Jerome M., et al.	438	593	02/20/2002
TT	US- 2003/0048666	03/13/2003	Eldridge, Jerome M., et al.	365	185.28	06/21/2002
TŢ	US- 2004/0004245	01/08/2004	Forbes, Leonard, et al.	257	315	07/08/2002
TŢ	US- 2004/0004247	01/08/2004	Forbes, Leonard, et al.	257	324	07/08/2002
TT	US- 2004/0004859	01/08/2004	Forbes, Leonard , et al.	365	185.05	07/08/2002
Tī	US-4,449,205	05/15/1984	Hoffman, Charles R.	365	182	02/19/1982
TT	US-4,495,219	01/22/1985	Kato, Takashi, et al.	427	82	10/08/1982
II	US-4,717,943	01/05/1988	Wolf, Hans P., et al.	357	23.5	07/16/1986
П	US-4,757,360	07/12/1988	Faraone, Lorenzo, et al.	357	23.5	07/06/1983
TT	US-4,794,565	12/27/1988	Wu, Albert T., et al.	365	185	09/15/1986
77	US-5,399,516	03/21/1995	Bergendahl, A., et al.	437	43	09/21/1992
11	US-5,455,792	10/03/1995	Yi, Yong-Wan	365	185.12	09/09/1994
TT	US-5,498,558	03/12/1996	Kapoor, A	437	43	05/06/1994
11	US-5,646,430	07/08/1997	Kaya, Cetin, et al.	257	322	08/28/1995
77	US-5,801,401	09/01/1998	Forbes, Leonard	257	77	01/29/1997
11	US-5,852,306	12/22/1998	Forbes, Leonard	257	315	01/29/1997

EXAMINER DATE CONSIDERED 07/21/04

PTO/SB08A(1001)
Approved for use through 10/31/2002, OMB 651-0031
Patent & Tradement Office: U.S. DEPARTMENT OF COMMERCE

Substitute Original 149A/PTO
INFORMATION DISCLOSURE
Application Number
Use a richy knowledge in recovery

Substitute Original 149A/PTO
INFORMATION DISCLOSURE
Application Number

Filing Date
August 30, 2001

First Named Inventor
Bhattacharyya, Arup

Group Art Unit
Examiner Name

Tran, Thien

Attorney Docket No: 1303.023US1

	,	<u> </u>		,	,	
777	US-5,923,056	07/13/1999	Lee, Woo-Hyeong, et al.	257	192	03/12/1998
TI	US-5,936,274	08/10/1999	Forbes, Leonard, et al.	257	315	07/08/1997
Π	US-5,952,692	09/14/1999	Nakazato, Kazuo , et al.	257	321	10/28/1997
TT	US-6,025,228	02/15/2000	Ibok, E., et al.	438	261	11/25/1997
TI	US-6,025,627	02/15/2000	Forbes, Leonard, et al.	257	321	05/29/1998
ŤΤ	US-6,031,263	02/29/2000	Forbes, Leonard, et al.	257	315	07/29/1997
717	US-6,069,380	05/30/2000	Chou, S. Y., et al.	257	315	07/25/1997
77	US-6,163,049	12/19/2000	Bui, N. D.	257	321	10/13/1998
TT	US-6,169,306	01/02/2001	Gardner, Mark I., et al.	257	310	07/27/1998
TT	US-6,210,999	04/03/2001	Gardner, Mark I., et al.	438	183	12/04/1998
77	US-6,229,175	05/08/2001	Uchida, Hidetsugu	257	315	03/19/1999
Π	US-6,246,606	06/12/2001	Forbes, Leonard, et al.	365	185.03	09/02/1999
Π	US-6,249,020	06/19/2001	Forbes, Leonard, et al.	257	315	08/27/1998
Π	US-6,249,460	06/19/2001	Forbes, Leonard, et al.	365	185.28	02/28/2000
TT	US-6,288,419	09/11/2001	Prall, Kirk D., et al.	257	213	07/09/1999
TT	US-6,307,775	10/23/2001	Forbes, Leonard , et al.	365	185.01	08/27/1998
71	US-6,351,411	02/26/2002	Forbes, Leonard, et al.	365	182	06/12/2001
П	US-6,424,001	07/23/2002	Forbes, Leonard, et al.	257	315	02/09/2001
TT	US-6,541,280	04/01/2003	Kaushik, Vidya S., et al.	438	3	03/20/2001
T	US-6,586,797	07/01/2003	Forbes, Leonard, et al.	257	325	08/30/2001

		FOREIGN PATENT	DOCUMENTS			
Examiner Initials'	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T³

EXAMINER	Thin	MIL.	DATE CONSIDERED	07/21/04	

PTO/SE/08A(10-01)
Approved for use through 10/31/2002, OA/8 651-0031
US Picent & Trademan Office, U.B. DEPARTMENT OF CONMERCE

	Under the Paperwork Reduction Act of 1995, no persons are	required to respond to a collection of information untess it contains a valid OMB control number			
Substitute for form 1448A/PTO	Complete if Known_	Complete if Known			
INFORMATION DISCLOSURE	Application Number	09/944985			
STATEMENT BY APPLICANT	Filing Date	August 30, 2001			
The same of the sa	First Named Inventor	Bhattacharyya, Arup			
MAY 1 7 2004	Group Art Unit	2811			
MAY 1 7 2004	Examiner Name	Tran, Thien			
Sheet 3 of 3	Attorney Docket No: 1	303.023US1			

	OTHE	R DOCUMENTS NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T
Tī		INUMIYA, S, et al., "Conformable formation of high quality ultra-thin amorphous Ta ₂ O ₅ gate dielectrics utilizing water assisted deposition (WAD) for sub 50 nm damascene metal gate MOSFETs", <u>IEDM Technical Digest. International Electron Devices Meeting</u> , (December 10-13, 2000),649-652	
TT		MANCHANDA, L., "Si-doped aluminates for high temperature metal-gate CMOS: Zr-Al-Si-O, a novel gate dielectric for low power applications", <u>IEDM Technical Digest. International Electron Devices Meeting</u> , (December 10-13, 2000),23-26	
П		YAMAGUCHI, TAKESHI, "Band Diagram and Carrier Conduction Mechanism in ZrO2/Zr-silicate/Si MIS Structure Fabricated by Pulsed-laser-ablation Deposition", Electron Devices Meeting, 2000. IEDM Technical Digest. International, (2000),19-22	

EXAMINER WIN MB DATE CONSIDERED 07/21/04-